

A Study of the Crystal Oscillator for CMOS-COPS™

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INTRODUCTION

The most important characteristic of CMOS-COPS is its low power consumption. This low power feature does not exist in TTL and NMOS systems which require the selection of low power IC's and external components to reduce power consumption.

The optimization of external components helps decrease the power consumption of CMOS-COPS based systems even more.

A major contributor to power consumption is the crystal oscillator circuitry.

Table I presents experimentally observed data which compares the current drain of a crystal oscillator vs. an external squarewave clock source.

The main purpose of this application note is to provide experimentally observed phenomena and discuss the selection of suitable oscillator circuits that cover the frequency range of the CMOS-COPS.

Table I clearly shows that an unoptimized crystal oscillator draws more current than an external squarewave clock. An RC oscillator draws even more current because of the slow rising signal at the CKI input.

Although there are few components involved in the design of the oscillator, several effects must be considered. If the requirement is only for a circuit at a standard frequency which starts up reliably regardless of precise frequency stability, power dissipation and etc., then the user could directly consult the data book and select a suitable circuit with proper components. If power consumption is a major requirement, then reading this application note might be helpful.

WHICH IS THE BEST OSCILLATOR CIRCUIT?

The Pierce Oscillator has many desirable characteristics. It provides a large output signal and drives the crystal at a low power level. The low power level leads to low power dissipation, especially at higher frequencies. The circuit has good short-term stability, good waveforms at the crystal, a frequency which is independent of power supply and temperature changes, low cost and usable at any frequency. As compared with other oscillator circuits, this circuit is not disturbed very much by connecting a scope probe at any point in the circuit, because it is a stable circuit and has low impedance. This makes it easier to monitor the circuit without any major disturbance. The Pierce oscillator has one disadvantage. The amplifier used in the circuit must have high gain to compensate for high gain losses in the circuitry surrounding the crystal.

TABLE I

A. Crystal oscillator vs. external squarewave COP410C change in current consumption as a function of frequency and voltage, chip held in reset, CKI is $\div 4$.

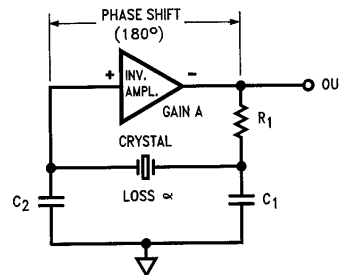
I = total power supply current drain (at V_{CC}).

Crystal			
V_{CC}	f_{ckl}	Inst. cyc. time	$I_{\mu A}$
2.4V	32 kHz	125 μs	8.5
5.0V	32 kHz	125 μs	83
2.4V	1 MHz	4 μs	199
5.0V	1 MHz	4 μs	360

External Squarewave			
V_{CC}	f_{ckl}	Inst. cyc. time	I
2.4V	32 kHz	125 μs	4.4 μA
5.0V	32 kHz	125 μs	10 μA
2.4V	1 MHz	4 μs	127 μA
5.0V	1 MHz	4 μs	283 μA

WHAT IS A PIERCE OSCILLATOR?

The Pierce is a series resonant circuit, and its basic configuration is shown below.



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FIGURE 1

For oscillation to occur, the Barkhausen criteria must be met: (1) The loop gain must be greater than one. (2) The phase shift around the loop must be 360° .

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Ideally, the inverting amplifier provides 180°, the R_1C_1 integration network provides a 90° phase lag, and the crystal's impedance which is a pure resistance at series resonance together with C_2 acts as a second integration network which provides another 90° phase lag. The time constants of the two RC phase shifting networks should be made as big as possible. This makes their phase shifts independent of any changes in resistance or capacitance values. However, big RC values introduce large gain losses and the selected amplifier should provide sufficient gain to satisfy gain requirement. CMOS inverters or discrete transistors can be used as amplifiers. An experimental evaluation of crystal oscillators using either type of amplifier is given within this report.

CRYSTAL OSCILLATORS USING CMOS-IC

The use of CMOS-IC's in crystal oscillators is quite popular. However, they are not perfect and could cause problems. The input characteristics of such IC's are good, but they are limited in their output drive capability.

The other disadvantage is the longer time delay in a CMOS-inverter as compared to a discrete transistor. The longer this time delay the more power will be dissipated. This time delay is also different among different manufacturers.

As a characteristic of most CMOS-IC's the frequency sensitivity to power supply voltage changes is high. As a group, IC's do not perform very well when compared with discrete transistor circuits.

But let us not be discouraged. Low component count which leads to low cost is one good feature of IC oscillators.

As a rule, IC's work best at the low end of their frequency range and poorest at the high end.

Several types of crystal oscillators using CMOS-IC's have been found to work satisfactorily in some applications.

CMOS—TWO INVERTER OSCILLATOR

The two inverter circuit shown in *Figure 2* is a popular one. The circuit is series resonant and uses two cascaded inverters for an amplifier.

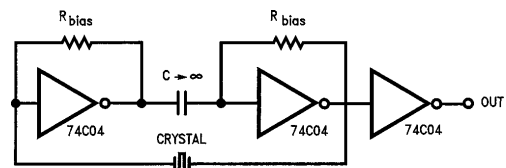


FIGURE 2

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Each inverter has a DC biasing resistor which biases the inverter halfway between the logic "1" and "0" states. This will help the inverters to amplify when the power is applied and the crystal will start oscillation.

The 74C family works better as compared with other CMOS-IC's. Will oscillate at a higher frequency and is less sensitive to temperature changes. The CMOS-COPS data sheet states that a crystal oscillator will typically draw 100 μ A more than an external clock source. However, the crystal oscillator described above will draw approximately as much

current as an external squarewave clock. The experimental data presented below shows the comparison:

Chip held in Reset, $V_{CC} = +5.0V$

$f = 455 \text{ kHz}$, COP444C, CKI is $\div 8$

Instruction cycle time = 17.5 μ s

I = total power supply (V_{CC}) current drain

Oscillator Type	I (current drain)
Crystal Osc. (data sheet)	950 μ A
Crystal Osc. (two inverter)	810 μ A
Ext. Clock	790 μ A

PIERCE IC OSCILLATOR

Figure 3 shows a Pierce oscillator using CMOS inverter as an amplifier.

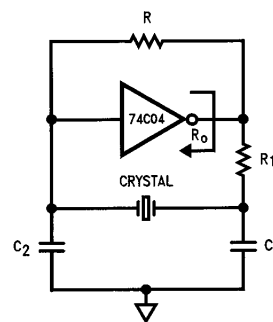


FIGURE 3

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The gain of CMOS inverter is low, so the resistor R_1 should be made small. This reduces gain losses. The output resistance of the inverter (R_o) can be the integrating resistor for the R_oC_1 phase lag network.

Omitting R_1 or with a small value of R_1 , the crystal will be driven at a much higher voltage level. This will increase power dissipation.

For lower frequencies (i.e., 32 kHz), R_1 must be large enough so that the inverter won't overdrive the crystal. Also, if R_1 is too large we won't get an adequate signal back at the inverter's input to maintain oscillation. With large values of R_1 the inverter will remain in its linear region longer and will cause more power dissipation. Typically for 32 kHz, R_1 should be constrained by the relation.

$$\frac{1}{2\pi R_1 C_1} \ll 32 \text{ kHz}$$

At higher frequencies, selection of R_1 is again critical. In order to drive a heavy load at high frequency, the amplifier output impedance must be low. In order to isolate the oscillator output from C_1 so it can drive the following logic stages, then R_1 should be large. But again, R_1 must not be too large, otherwise it will reduce the loop gain.

The value of R_1 is chosen to be roughly equal to the capacitive reactance of C_1 at the frequency of operation, or the value of load impedance Z_L .

$$\text{Where } Z_L = \frac{X_{C1}^2}{R_L}$$

$R_L = R_S =$ series resistance of crystal

The small values of C_1 and C_2 will help minimize the gain reduction they introduce.

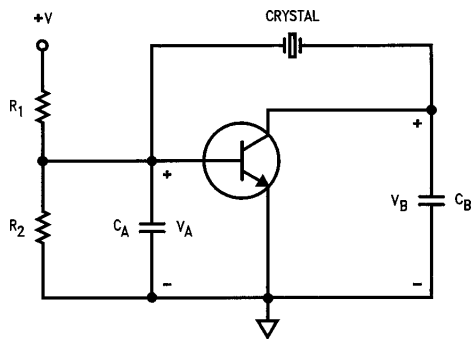
typically: $C_1 = C_2 = 220 \text{ pF}$ at 1 MHz

$C_1 = C_2 = 330 \text{ pF}$ at 2 MHz

DISCRETE TRANSISTOR OSCILLATOR

As mentioned earlier, a discrete transistor circuit performs better than an IC circuit. The reason for this is that in a discrete transistor circuit it is easier to control the crystal's source and load resistances, the gain and signal amplitude.

A discrete transistor circuit has shorter time delay, because it uses one or two transistors. This time delay should always be minimized, since it causes more power dissipation and shifts frequency with temperature changes. *Figure 4* shows a basic Pierce oscillator using a transistor as an amplifier.



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FIGURE 4

The basic phase shift network consists of C_{A1} , C_{B2} and the crystal which looks inductive and is series resonant with C_{A1} and C_{B1} . The phase shift through the transistor is 180° and the total phase shift around the loop is 360° . The condition of a unity loop gain must also be satisfied.

$$\frac{V_A}{V_B} = -\left(\frac{C_B}{C_A}\right)$$

$$\frac{V_A}{V_B} = -\left(\frac{X_{CA}}{X_{CB}}\right)$$

For oscillation to occur, the transistor gain must satisfy the relation

$$G\left(\frac{V_A}{V_B}\right) \geq 1$$

where $G = -g_{fe}Z_L$

g_{fe} is the transconductance of the transistor

Z_L is the load seen by the collector

$$Z_L = \frac{X_B^2}{R_e}, \quad X_B = -\frac{1}{WC_B}$$

R_e is the crystal's effective series resistance.

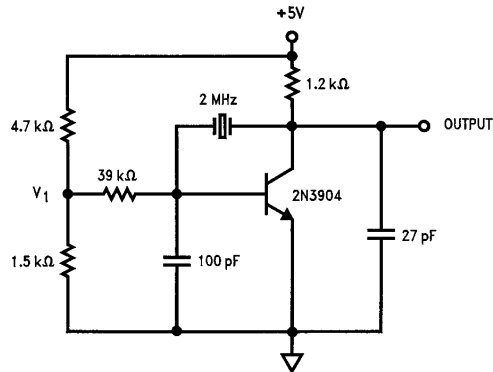
The crystal's drive level

$$P_d = \frac{V_B^2 R_e}{X_B^2}$$

This drive level should not exceed the manufacturer's spec.

Certain biasing conditions might cause collector saturation. Collector saturation increases oscillator's dependence on the supply voltage and should be avoided.

The circuit of *Figure 5* has been tested and has a very good performance.



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FIGURE 5

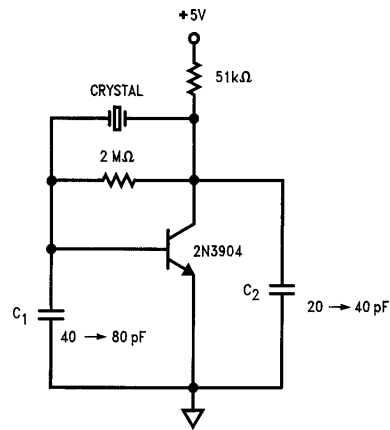
This circuit will oscillate over a wide range of frequencies 2-20 MHz.

$$\text{Voltage } (V_1) = \frac{(5)(1.5)}{1.5 + 4.7} = 1.21V$$

$$\text{Base Current} = \frac{1.21 - V_{BE}}{39k} = 15.6 \mu A$$

At Saturation ($V_{CE} = 0$)

$$I_C (\text{SAT}) = \frac{5}{1.2} = 4.2 \text{ mA}$$



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FIGURE 6

Having 15.6 μA of base current, for saturation to occur

$$h_{FE} = \frac{4.2 \text{ mA}}{15.6 \mu\text{A}} = 269$$

The DC beta for 3904 at 1 mA is 70 to 210, so no problem with saturation, even at lower supply voltages.

The current consumption (power supply V_{CC} current drain) of COP444C using the above oscillation circuit is around 267 μA .

The circuit of *Figure 6* is another configuration of discrete transistor oscillator.

The performance of above circuit is also good. The only drawback is that it does not provide larger output signal.

CONCLUSION

As discussed within this report, a discrete transistor circuit gives better performance than an IC circuit. However, oscillators using discrete transistors are more expensive than those using IC's when assembly labor costs are included. So, the selection of either circuit is a trade-off between better performance and cost.

The data and circuits presented here are intended to be used only as a guide for the designer. The networks described are generally simple and inexpensive and have all been observed to be functional. They only provide greater flexibility in the oscillator selection for CMOS-COPS systems.

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